

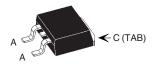
HiPerFRED™ Epitaxial Diode with soft recovery

V RRM	=	300
\mathbf{t}_{rr}	=	35

V _{RSM}	V _{RRM}	Туре
300	300	DSEP 40-03AS



TO-263



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAVM}	rect., $d = 0.5$; $T_C = 120^{\circ}C$	40	Α
I _{FSM}	$T_{VJ} = 45^{\circ}C$; $t_p = 10$ ms (50 Hz), sine	300	Α
E _{AS}	$T_{VJ} = 25^{\circ}\text{C}$; non-repetitive $I_{AS} = 9 \text{ A}$; L = 100 μH	4	mJ
I _{AR}	V _A = 1.5⋅V _R typ.; f = 10 kHz; repetitive	0.9	Α
T _{VJ}		-40+175	°C
T_{VJM}		175	°C
T_{stg}		-40+150	°C
P _{tot}	$T_C = 25^{\circ}C$	175	W
Weight	typical	2	g

Symbol	Conditions	Characteristic max. Values	
I _R ①	$V_R = V_{RRM}; T_{VJ} = 25^{\circ}C$ $V_R = V_{RRM}; T_{VJ} = 150^{\circ}C$	1 100	μA μA
V _F ②	$I_F = 40 \text{ A}; \qquad T_{VJ} = 150^{\circ}\text{C}$ $T_{VJ} = 25^{\circ}\text{C}$	1.11 1.42	V
R _{thJC}		0.85	K/W
t _{rr} typ.	$ \begin{cases} V_R = 100 \text{ V}; & I_F = 40 \text{ A}; \\ -di_F/dt = 200 \text{ A/}\mu\text{s}; T_{VJ} = 25^{\circ}\text{C} \end{cases} $	35 3.5	ns A

Pulse test: ① Pulse Width = $\,$ 5 ms, Duty Cycle < 2.0% ② Pulse Width = 300 μ s, Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified.

Features

International standard package

- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- · Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Dimensions see Outlines.pdf